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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Ichio YUDASAKA et al.

Application No.: 09/936,041

Filed: December 18, 2001

For: METHOD FOR MANUFACTURING A THIN-FILM TRANSISTOR COMPRISING A RECOMBINATION CENTER (AS AMENDED)

Group Art Unit: 2812

Examiner: Angel Roman

Docket No.: 110553

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TECHNOLOGY CENTER 2800

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the April 2, 2002 Office Action, please amend the above-identified application as follows:

IN THE TITLE:

Please replace the title so that it reads as follows:

METHOD FOR MANUFACTURING A THIN-FILM TRANSISTOR
COMPRISING A RECOMBINATION CENTER.

IN THE CLAIMS:

Please replace claims 1-2 and 7-13 as follows:

The following is a marked-up version of the amended claims:

1. (Twice Amended) A method of manufacturing a thin-film transistor, comprising:
forming a channel region facing a gate electrode through a gate insulating film;